

P-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY

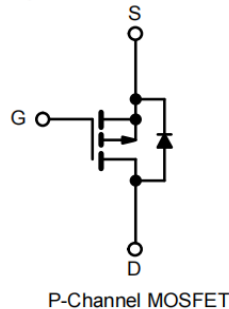
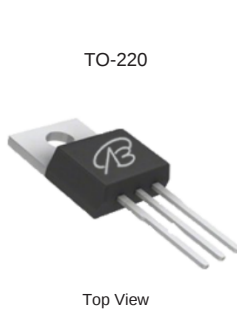
V_{DS} (V)	$R_{DS(on)}$ (Ω) MAX.	I_D (A)	Q_g (TYP.)
-100	0.035at $V_{GS} = -10V$	-35	75nC

FEATURES

- SGT technology Power MOSFET
- 100 % R_g and UIS tested
- Maximum 150°C junction temperature



RoHS
COMPLIANT
HALOGEN
FREE



APPLICATIONS

- Power supplies:
 - Uninterruptible power supplies
 - AC/DC switch-mode power supplies
 - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Solar micro inverter
- Class D audio amplifier

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	-100	V
Gate-Source Voltage		V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	I _D	-35	A
	T _C = 70 °C		-30	
Pulsed Drain Current (t = 100 μs)		I _{DM}	-105	
Avalanche Current	L = 0.5 mH	I _{AS}	-75	
Single Avalanche Energy ^a		E _{AS}	-760	mJ
Maximum Power Dissipation ^a	T _C = 25 °C	P _D	300 ^b	W
	T _C = 100 °C		150 ^b	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient (PCB Mount) ^c	R_{thJA}	40	$^{\circ}\text{C/W}$
Junction-to-Case (Drain)	R_{thJC}	0.5	

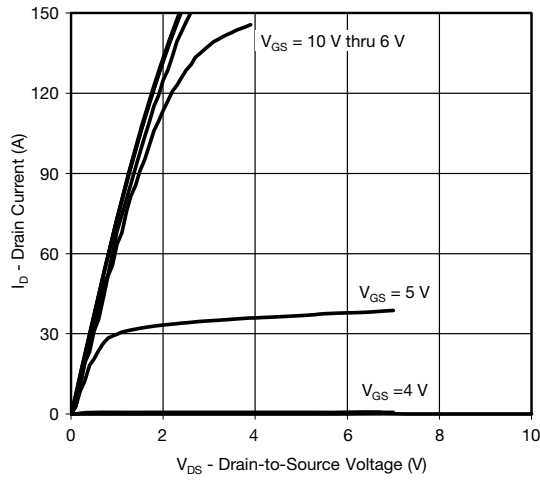
Notes

- Duty cycle $\leq 1\%$.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR4 material).

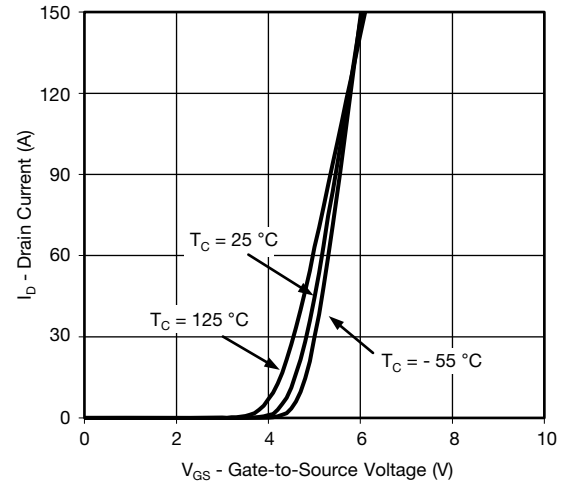
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	-100	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	-2.5	-	-4.5	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	-	-	± 250	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -100 V, V _{GS} = 0 V	-	-	-1	μA
		V _{DS} = -100 V, V _{GS} = 0 V, T _J = 125 °C	-	-	-150	
		V _{DS} = -50 V, V _{GS} = 0 V, T _J = 150 °C	-	-	-5	mA
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 10 V, V _{GS} = -10 V	-90	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = -30 A	-	0.035	-	Ω
		V _{GS} = 7.5 V, I _D = -20 A	-	0.038	-	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = -30 A	-	75	-	S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = -80 V, f = 1 MHz	-	3600	-	pF
Output Capacitance	C _{oss}		-	246	-	
Reverse Transfer Capacitance	C _{rss}		-	21	-	
Total Gate Charge ^c	Q _g	V _{DS} = -80 V, V _{GS} = -10 V, I _D = -60 A	-	60	96	nC
Gate-Source Charge ^c	Q _{gs}		-	16.7	-	
Gate-Drain Charge ^c	Q _{gd}		-	16.9	-	
Gate Resistance	R _g	f = 1 MHz	1.5	3	6	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = -80 V, R _L = 1.66 Ω I _D ≅ 60 A, V _{GEN} = -10 V, R _g = 1 Ω	-	15	27	ns
Rise Time ^c	t _r		-	105	210	
Turn-Off Delay Time ^c	t _{d(off)}		-	36	78	
Fall Time ^c	t _f		-	80	145	
Drain-Source Body Diode Ratings and Characteristics ^b (T _C = 25 °C)						
Pulsed Current (t = 100 μs)	I _{SM}		-	-	-105	A
Forward Voltage ^a	V _{SD}	I _F = -10 A, V _{GS} = 0 V	-	-0.8	-1.2	V
Reverse Recovery Time	t _{rr}	I _F = -30 A, di/dt = 100 A/μs	-	30	-	ns
Peak Reverse Recovery Charge	I _{RM(REC)}		-	11	20	A
Reverse Recovery Charge	Q _{rr}		-	0.9	1.8	μC

Notes

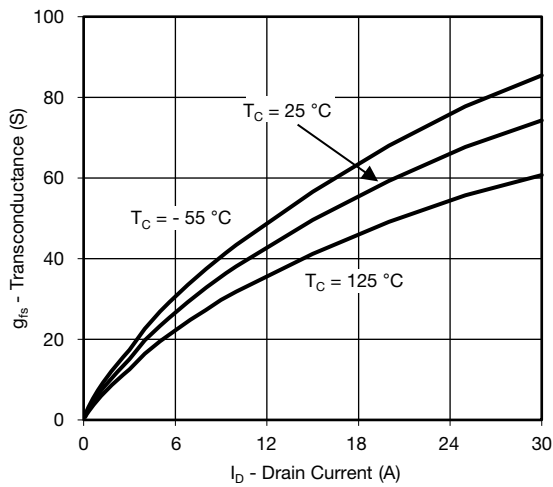
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.
 c. Independent of operating temperature.

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)


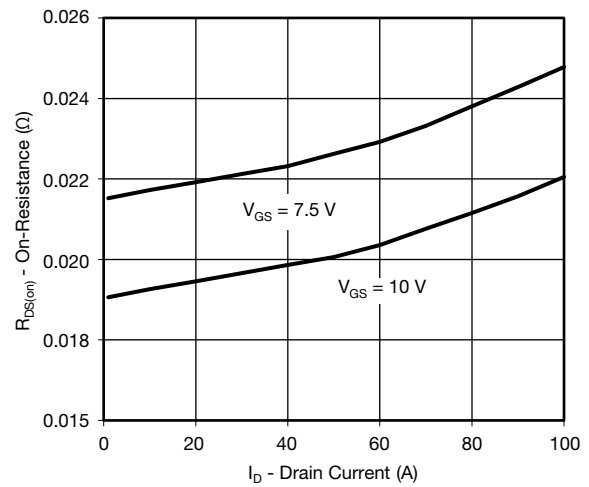
Output Characteristics



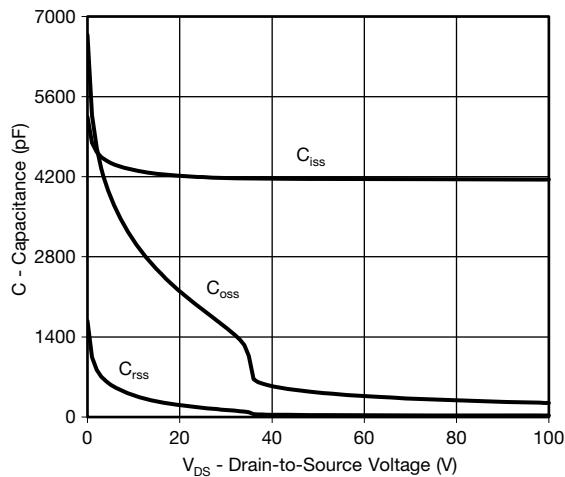
Transfer Characteristics



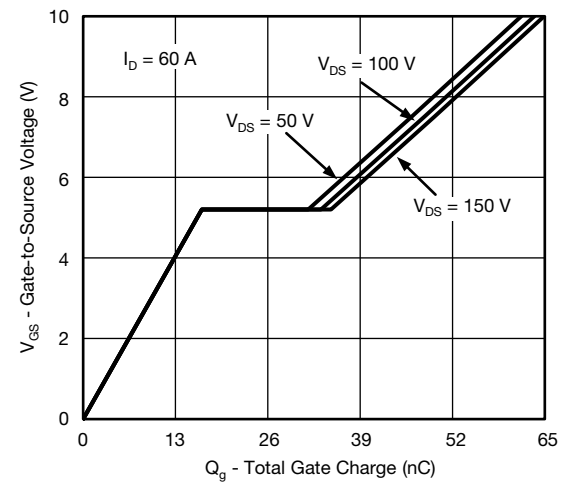
Transconductance



On-Resistance vs. Drain Current

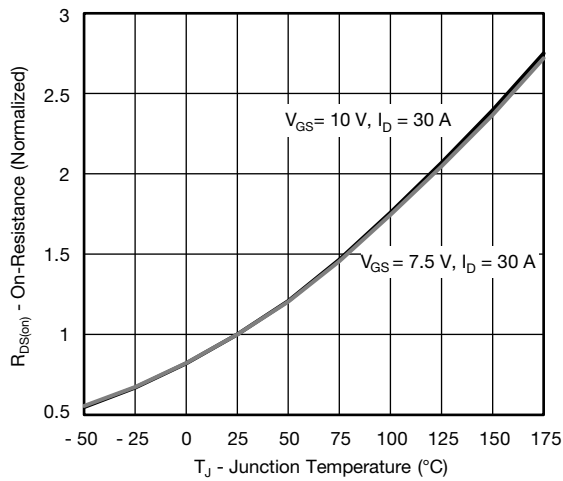


Capacitance

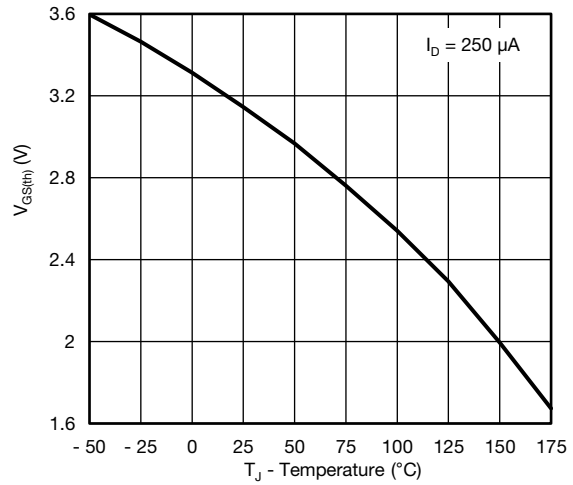


Gate Charge

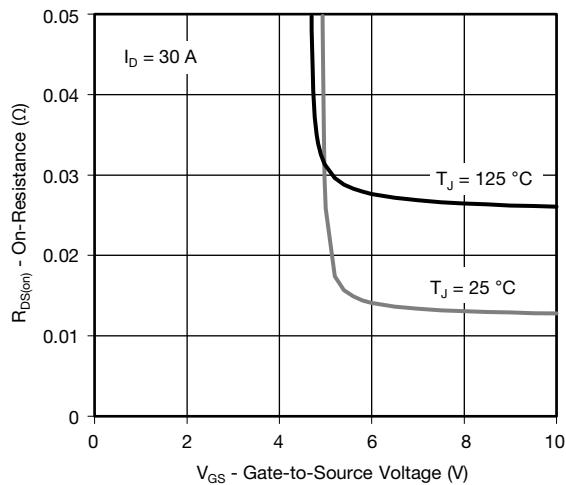
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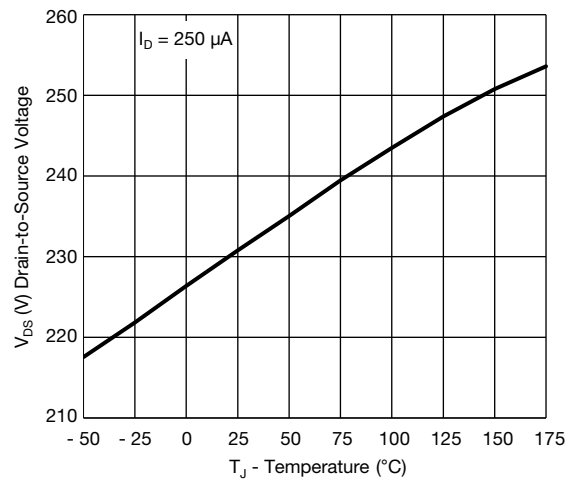
On-Resistance vs. Junction Temperature



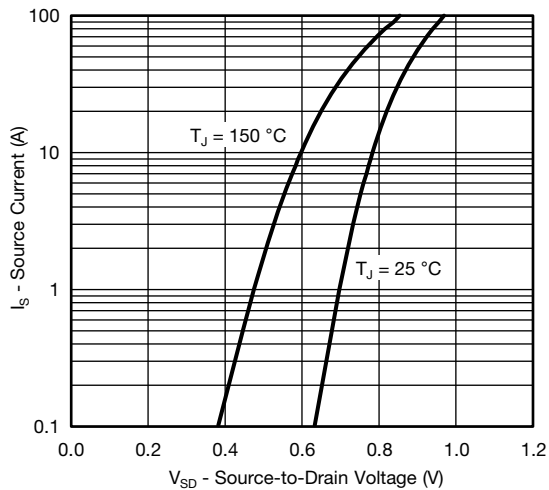
Threshold Voltage



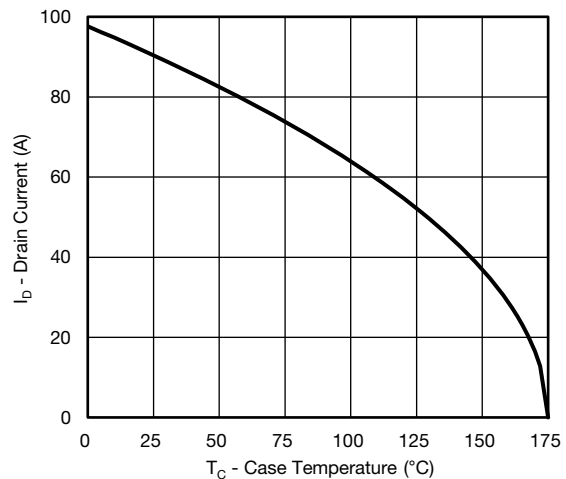
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

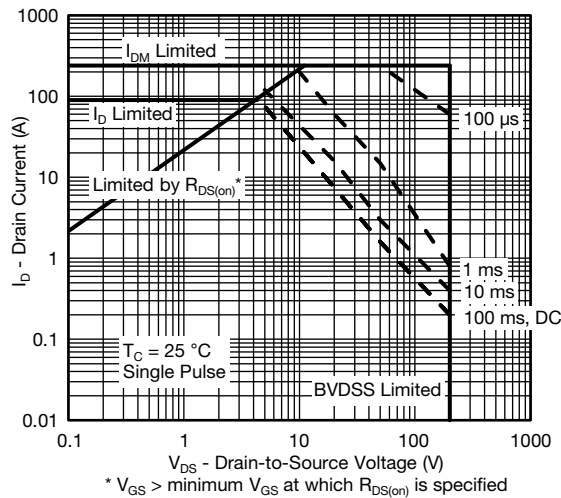


Source Drain Diode Forward Voltage

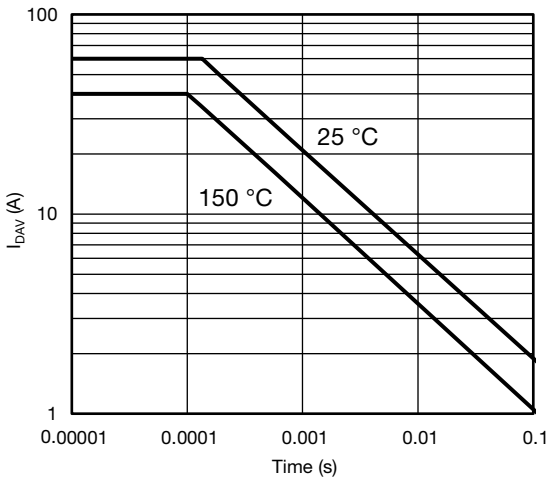


Current De-rating

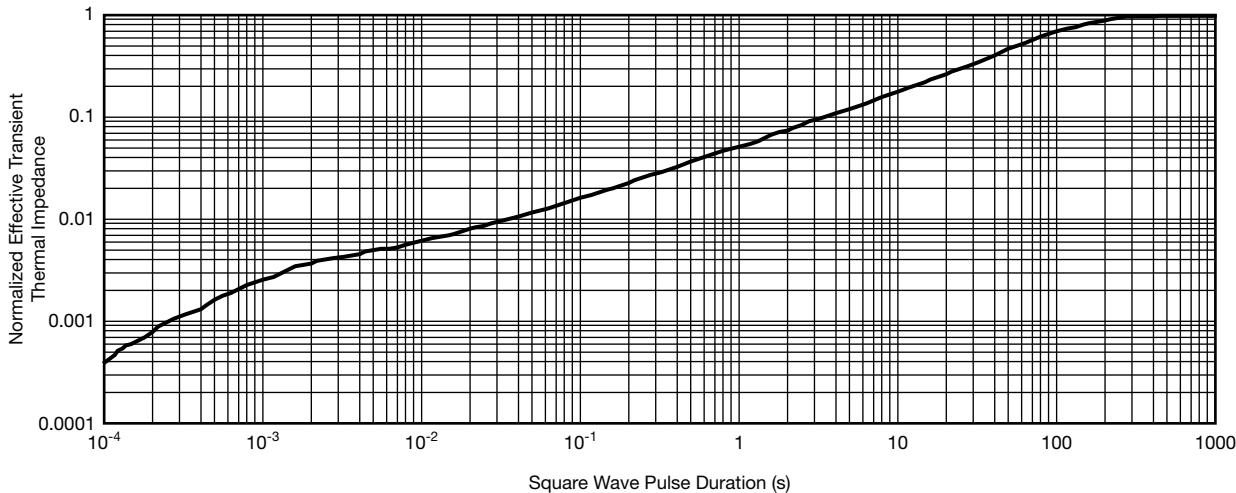
THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



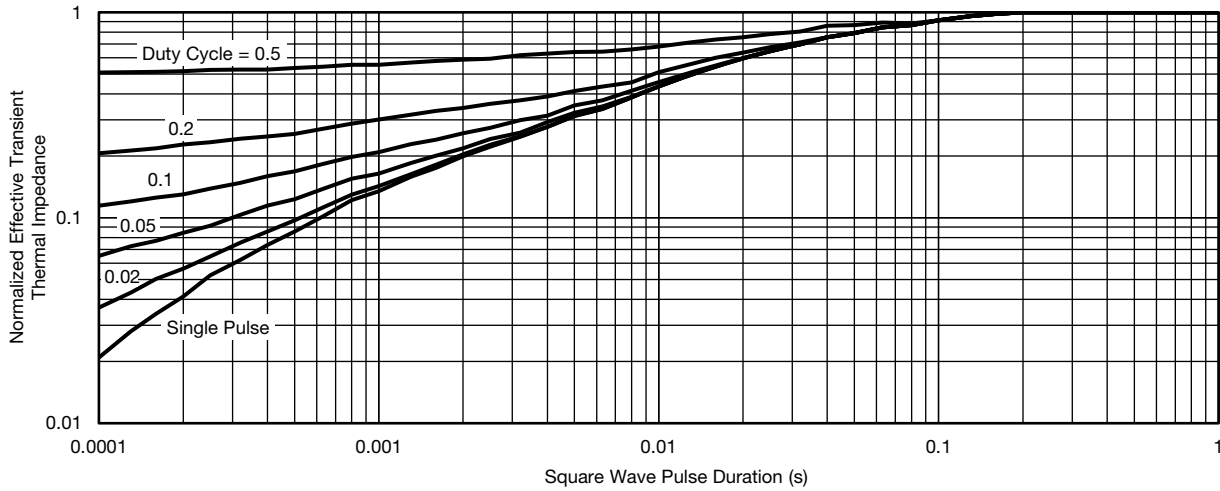
Safe Operating Area



Single Pulse Avalanche Current Capability vs. Time



Normalized Thermal Transient Impedance, Junction-to-Ambient

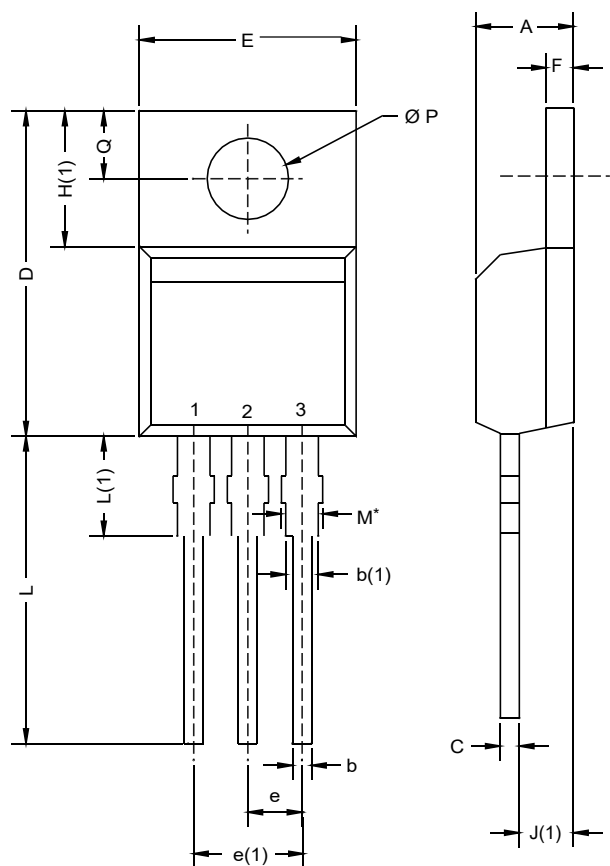
THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)


Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction to Case ($25\text{ }^{\circ}\text{C}$)
- are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118
ECN: X12-0208-Rev. N, DWG: 5471				

Notes

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
 Heatsink hole for HVM

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